

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,955,940 B2  
DATED : October 18, 2005  
INVENTOR(S) : Kristy A. Campbell et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, FOREIGN PATENT DOCUMENTS,

"WO 97/488032" should read -- WO 97/48032 --.

OTHER PUBLICATIONS,

"Hirose, et al , "Polanty-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous  $\text{As}_2\text{S}_3$  films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pps 2767-2772."

should read

-- Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous  $\text{As}_2\text{S}_3$  films", Journal of Applied Physics. Vol. 47. No. 6. Jun. 1976. pps 2767-2772. --.

"Kluge, et al , "Silver photodiffusion in amorphous  $\text{Ge}_x\text{Se}_{100-x}$ ", Journal of Non-Crystalline Solids 124 (1990) pps 186-193."

should read

-- Kluge, et al., "Silver photodiffusion in amorphous  $\text{Ge}_x\text{Se}_{100-x}$ ", Journal of Non-Crystalline Solids 124 (1990) pps 186-193. --;

"Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances n Physics No. 6, 475-588 (Taylor & Francis 1995)."

should read

-- Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995). --;

"Drusedau, T.P.; Panckow, A.N.; Klabunda, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832."

should read

-- Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832. --;

"Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucal, J., Identation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269."

should read

-- Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269. --;

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Title page (cont'd),

"Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoel, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52."

should read

-- Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52. --.

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe<sub>2</sub> Crystals, Science 258 (1992) 271-274."

should read

-- Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-temperature, electric field induced creation of stable devices in CuInSe<sub>2</sub> crystals, Science 258 (1992) 271-274. --;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

should read

-- Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146. --;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Legarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985."

should read

-- Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors. Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985. --.

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."

should read

-- Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080. --.

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Title page (cont'd).

Item [74], *Attorney, Agent, or Firm*, "Dickstein Shaprio Morin & Oshinsky LLP" should read -- Dickstein Shapiro Morin & Oshinsky LLP --.

Item [57], **ABSTRACT**,

Line 10, "to and HNO<sub>3</sub>" should read -- to an HNO<sub>3</sub> --.

Column 3,

Line 45, "example only, example" should read -- example only, --.

Column 6,

Line 52, "comprises and oxide" should read -- comprises an oxide --.

Column 9,

Line 17, "atomosphere" should read -- atmosphere --.

Signed and Sealed this

Twenty-first Day of March, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looping initial "J" and a distinct "D".

JON W. DUDAS  
*Director of the United States Patent and Trademark Office*